



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q61741

Takashi UDAGAWA

Appln. No.: 09/881,782

Group Art Unit: 2815

Confirmation No.: 1610

Examiner: Paul E. Brock II

Filed: June 18, 2001

For: GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE, LIGHT
EMITTING DIODE LAMP, LIGHT SOURCE, ELECTRODE FOR GROUP-III NITRIDE
SEMICONDUCTOR LIGHT-EMITTING DIODE, AND METHOD FOR PRODUCING
THE ELECTRODE

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 25, 2002, please amend the above-identified
application as follows:

IN THE CLAIMS:

Please cancel claim 22 without prejudice or disclaimer.

Please enter the following amended claims:

1. (Twice Amended) A group-III nitride semiconductor light-emitting diode comprising
at least a first conduction-type single crystal substrate provided with a first conduction-type
back-surface ohmic electrode on a back surface thereof, a buffer layer comprising a boron
phosphide (BP)-based material on a front surface of said single crystal substrate, a gallium
nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction

2815
#14/C
10/30/02
Burley

RECEIVED
OCT 28 2002
TECHNOLOGY CENTER 2800

sub D.1
C1